

60. [(New)] A physical vapor deposition target comprising an alloy of copper and one or more other elements, the one or more other elements being present in the alloy at a total concentration from less than 1.0 at% to 0.001 at% and being selected from the group consisting of Sr, Ba, Sc, and Se.

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61. [(New)] The physical vapor deposition target of claim 60 wherein the one or more other elements are present in the alloy at a total concentration at from 0.005 at% to 0.1 at%.

62. [(New)] The physical vapor deposition target of claim 60 comprising an RF sputtering coil.

63. [(New)] The physical vapor deposition target of claim 60 wherein the element comprises Sr.

64. [(New)] The physical vapor deposition target of claim 60 wherein the element comprises Ba.

65. [(New)] The physical vapor deposition target of claim 60 wherein the element comprises Sc.

66. [(New)] The physical vapor deposition target of claim 60

B¹ wherein the element comprises Se.

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